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Charge-Based Continuous Equations for the Transconductance and Output Conductance of Graded-Channel SOI MOSFET's

M. de Souza and M. A. Pavanello

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FOREWORD

This issue of Journal of Integrated Circuits and Systems (JICS) includes 8 papers on process, materials, devices, and modeling. These papers have been selected from the presentations given at SBMicro2006 (Symposium on Microelectronics Technology and Devices), which was organized in Ouro Preto, Brazil in 2006. Among the contributions presented at SBMicro2006 conference, only a few were selected by the Technical Committee for this issue. These papers have been submitted to usual reviewing process with the help of external experts.

We would like to thank the authors for their effort in preparing these high quality papers, as well as the reviewers for their help on paper selection which guarantees the scientific level of this issue. We sincerely hope that JICS readers will enjoy these contributions, as we have enjoyed listening to them at the SBMicro2006 conference.

The Editors.



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